	Type	Hits	Search Text	DBs
1	BRS	69315	MOSFET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
2	BRS	1113	MOSFET and salicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
3	BRS	335	(MOSFET and salicide) and (amorph$8 with silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
4	BRS	186	(MOSFET and salicide) and (cobalt adj (salicide or silicide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
5	BRS	141	((MOSFET and salicide) and (cobalt adj (salicide or silicide))) and anneal$4 and etch$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
6	BRS	18	(((MOSFET and salicide) and (cobalt adj (salicide or silicide))) and anneal$4 and etch$4) and (second adj anneal$4) and etch$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
7	BRS	1	((((MOSFET and salicide) and (cobalt adj (salicide or silicide))) and anneal$4 and etch$4) and (second adj anneal$4) and etch$4) and (amorph$8 with depth)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
8	BRS	1	((((MOSFET and salicide) and (cobalt adj (salicide or silicide))) and anneal$4 and etch$4) and (second adj anneal$4) and etch$4) and (amorph$8 with (profindity or penetration or sagacity or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
9	BRS	10	((((MOSFET and salicide) and (cobalt adj (salicide or silicide))) and anneal$4 and etch$4) and (second adj anneal$4) and etch$4) and depth	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
10	BRS	414	MOSFET and (salicide or silicide) and (cobalt adj (salicide or silicide)) and anneal$4 and etch$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
11	BRS	37	(MOSFET and (salicide or silicide) and (cobalt adj (salicide or silicide)) and anneal$4 and etch$4) and (second adj anneal$4) and etch$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Time Stamp	Comments	Error Definition	Errors
1	2004/02/07 14:45			0
2	2004/02/07 14:48			0
3	2004/02/07 14:50			0
4	2004/02/07 14:51			0
5	2004/02/09 12:48			0
6	2004/02/09 12:50			0
7	2004/02/07 15:23			0
8	2004/02/09 12:54			0
9	2004/02/09 12:55			0
10	2004/02/09 12:50			0
11	2004/02/09 12:51			0

	Type	Hits	Search Text	DBs
12	BRS	1	((MOSFET and (salicide or silicide) and (cobalt adj (salicide or silicide)) and anneal$4 and etch$4) and (second adj anneal$4) and etch$4) and (amorph$8 with (profindity or penetration or sagacity or depth))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
13	BRS	18	((MOSFET and (salicide or silicide) and (cobalt adj (salicide or silicide)) and anneal$4 and etch$4) and (second adj anneal$4) and etch$4) and depth	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
14	BRS	2	(((MOSFET and (salicide or silicide) and (cobalt adj (salicide or silicide)) and anneal$4 and etch$4) and (second adj anneal$4) and etch$4) and depth) and recrystal$8	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Time Stamp	Comments	Error Definition	Errors
12	2004/02/09 12:55			0
13	2004/02/09 12:57			0
14	2004/02/09 12:58			0